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IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Application of: Small, Robert J. et al.

Confirmation No.: 9378

Application No.: 09/903,064

Group Art Unit: 1751

Filed: July 10, 2001

Examiner: Webb, Gregory E.

For:

Compositions for Cleaning Organic

Attorney Docket No.: 60937-091-US

and Plasma Etched Residues for

(formerly 8317-091-999)

Semiconductor Devices

TRANSMITTAL OF POWER OF ATTORNEY BY ASSIGNEE REVOKING PREVIOUS POWERS OF RECORD

Commissioner for Patents P.O. Box 1450 Alexandria, VA 22313-1450

Sir:

Applicants' attorney encloses herewith a Revocation and Power of Attorney by Assignee for the above identified application.

<u>Please change the attorney docket number to 60937-091-US</u>. Future correspondence should be forwarded to James S. McDonald, customer no. **24341**.

No fee is believed due at this time, however, the Commissioner is authorized to charge any fees associated with this communication to Morgan, Lewis & Bockius LLP Deposit Account No. 50-0310 (Order No. 60937-091-US). A copy of this sheet is enclosed for such purpose.

Respectfully submitted,

Date March 12, 2004

James S. McDonald

(Reg. No. 44,229)

MORGAN, LEWIS & BOCKIUS LLP

3300 Hillview Avenue Palo Alto, CA 94304

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REVOCATION AND POWER OF ATTORNEY

Commissioner for Patents P.O. Box 1450 Alexandria, VA 22313-1450

SIR:

EKC Technology, Inc., owner of the entire right, title and interest in, to and under the inventions described and claimed in the patent applications identified in the attached Schedule A, hereby revokes all previous powers of attorney and appoints Morgan, Lewis & Bockius LLP, customer no. 24341, and each of them, its attorneys, to prosecute each of these patent applications, and to transact all business in the Patent and Trademark Office connected therewith.

Please direct all future correspondence to Customer Number 24341, Morgan, Lewis & Bockius LLP, located at 3300 Hillview Avenue, Palo Alto, California 94304, and direct all telephone calls to Morgan, Lewis & Bockius LLP at (650) 493-4935.

Assignee:

EKC Technology, Inc.

Date:

7 Feb 2004

Signature:

Michael A. Fury

Typed Name: Position/Title:

Vice President, R&D and Engineering

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2520 Barrington Court Hayward, CA 94545

Schedule A					
App.#	Title	inventor(s)	Filling Date	New Attorney. Docket No.	Former Attorney Docket No.
	Compositions for Cleaning Organic				
	and Plasma Etched Residues for				
09/903,064	Semiconductor Devices	Small, et al.	07/10/2001	60937-091-US	8317-091-999
00/974 220	Method of and Apparatus for Substrate Pre-Treatment	Molemen, et el	00/00/0004	00007 444 110	004= 444 000
09/874,330	Chemical Mechanical Polishing	Maloney, et al.	06/06/2001	60937-111-US	8317-111-999
09/985,870	Compositions	Small, et al.	11/06/2001	60937-114-US	8317-114-999
, , , , , , , , , , , , , , , , , , ,	Oxalic Acid as a Semiaqueous	Oman, ct al.	11/00/2001	00337-114-03	0317-114-999
	Cleaning Product for Copper and				
10/421,706	Dielectrics	Lee, et al.	04/24/2003	60937-116-US	8317-116-999
	Sulfoxide Pyrolid(in)one Alkanolamine	•			
10/193,185	Cleaner Composition	Zhou, et al.	07/12/2002	60937-118-US	8317-118-999
	Method for the Deposition of Materials				
09/876,944	from Mesomorphous Films	Vasquez, et al.	06/08/2001	60937-120-US	8317-120-999
10/007 124	Post Etch Cleaning Composition for	5	10/01/0001		
10/007,134	Dual Damascene System Photolytic Conversion Process to	Payne, et al.	12/04/2001	60937-123-US	8317-123-999
10/263,701	Form Patterned Amorphous Film	Bravo-Vasquez, et al.	10/04/2002	60937-126-US	9247 400 000
10/203,701	Cleaning Solutions Including	bravo-vasquez, et al.	10/04/2002	00937-120-05	8317-126-999
	Nucleophilic Amine Compound				
	Having Reduction and Oxidation				
09/988,545	Potential	Lee, et al.	.11/20/2001	60937-127-US	8317-127-999
	Method and Compositions for				
	Chemically Treating A Substrate			,	
10/060,109	Using Foam Technology	Patel, et al.	01/28/2002	60937-129-US	8317-129-999
	Cleaning Solution Including				
	Nucleophilic Amine Compound				
10/125 605	Having Reduction and Oxidation	1 4 - 1	05/04/0000	00007 405 440	2017 125 222
10/135,695	Potential Fluoride Layer and Removing Same	Lee, et al. Melvin K. Carter	05/01/2002	60937-135-US	8317-135-999
10/440,127		Melvin K. Carter	05/30/2003	60937-137-US	8317-137-999
	Process for the Use of Bis-Choline				
1	and Tris-Choline in the Cleaning of Quartz-Coated Polysilicon and Other				
10/689,657	Materials	Charm, et al.	10/22/2003	60027 120 110	9247 420 000
10/003,03/	Cleaning Compositions Containing	Chain, et al.	10/22/2003	60937-139-US	8317-139-999
	Hydroxylamine Derivatives and				
	Process Using Same for Residue				
10/689,620	Removal	Zhou, et al.	10/22/2003	60937-140-US	8317-140-999
	Composition for Exfoliation Agent to				
10/689,616	be Used to Remove Resist Residues	Melvin K. Carter	10/22/2003	60937-141-US	8317-141-999
	Reducing Oxide Loss When Using				
	Fluoride Chemistries to Remove Post-				
60/467 124	Etch Residues in Semiconductor	100 -1-1	05/02/2222	00007 440 05	0047 440 000
60/467,131	Processing	Lee, et al.	05/02/2003	60937-142-PR	8317-142-888

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			Filing	New Attorney	Former Attorney
App #		Inventor(s) *	Date ::	Docket No:	Docket No. 4
10/000 001	Method for Depositing Patterned				
10/630,301	Films of Materials	Hill, et al.	07/30/2003	60937-143-US	8317-143-999
,	Methods for the Deposition of Silver				
10/716 020	and Silver Oxide Films and Patterned	Dunn of al	44/40/0000	60007 447 110	
10/716,838	Films Semiconductor Process Residue	Ruan, et al.	11/18/2003	60937-147-US	8317-147-999
10/162,679	Removal Composition and Process	Lee, et al.	06/06/2002	60937-149-US	9247 440 000
10/102,0/3	System and Method for Cleaning	Lee, et al.	00/00/2002	00937-149-03	8317-149-999
	Workpieces Using Supercritical				
60/469,826	Carbon Dioxide	Fury, et al.	05/13/2003	60937-150-PR	8317-150-888
			00.10.2000	00001 100 110	0017 100 000
	Abrasive-Free Chemical Mechanical				
,	Polishing Composition and Polishing				
10/689,043	Process Containing Same	Yao, et al.	10/21/2003	60937-151-US	8317-151-999
10/689,042	Wet Etch of Titanium-Tungsten Film	Patel, et al.	10/21/2003	60937-152-US	8317-152-999
	Method of Depositing Nanostructured				
10/261,197	Films with Embedded Nanopores	Svendsen, et al.	09/30/2002	60937-153-US	8317-153-999
40/200 270	Hydrothermal Treatment of	Mariahan dan akan	40/00/0000	00007.407.440	
10/280,270	Nanostructured Films Inhibition of Titanium Corrosion	Mukherjee, et al.	10/23/2002	60937-167-US	8317-167-999
10/257,469	Chemical Mechanical Polishing	Daviot, et al.	10/11/2002	60937-168-US	8317-168-999
10/401,405	Composition and Process	Small, et al.	03/27/2003	60937-171-US	8317-171-999
10/401,400	Aqueous Phosphoric Acid	Oman, et al.	03/2/12003	00937-171-03	0317-171-999
	Compositions for Cleaning				
10/688,900	Semiconductor Devices	Daviot, et al.	10/21/2003	60937-172-US	8317-172-999
	Load Lock System for Supercritical			00001 1.12 00	
10/465,906	Fluid Cleaning	Fury, et al.	06/18/2003	60937-175-US	8317-175-999
	Automated Dense Phase Fluid				
10/465,905	Cleaning System	Fury, et al.	06/18/2003	60937-176-US	8317-176-999
	Residue Removers for				
	Electrohydrodynamic Cleaning of				
60/455,439	Semiconductors	Robert J. Small	03/18/2003	60937-178-PR	8317-178-888
	Free Radical-Forming Activator				
	Attached to Solid and Used to				
10/361,822	Enhance CMP Formulations	Scott, et al.	02/11/2003	60937-179-US	8317-179-999
40/077 500	Titanium Carboxylate Films for Use in				
10/377,533	Semiconductor Processing	Hill, et al.	02/26/2003	60937-182-US	8317-182-999
10/422,860	Method of Making Barrier Layers	Maloney, et al.	05/20/2003	60937-183-US	8317-183-999
	Remover Formulation Containing Fluoride for Use During				
60/463,739	Semiconductor Manufacturing	Hirasawa, et al.	04/18/2003	60937-185-PR	8317-185-888
30, 100,709	Cleaning Composition for Removing	i ili asawa, ci al.	04/10/2003	00301-100-FR	0317-100-000
	Resists and Manufacturing Method of				
60/464,125	Semiconductor Devices	Hirasawa, et al.	04/21/2003	60937-186-PR	8317-186-888
	Deposition of Permanent Polymer				
10/422,212	Structures for OLED Fabrication	Roman, et al.	04/23/2003	60937-187-US	8317-187-999

77796 W. W. C.		**************************************		PROPERTY AND STREET	Process village synthetic
App.# 4.4	Title :	linventor(s)	Filing aDate	New Attorney Docket No.	Former Attorney Docket No.
	Seimconductor Process Residue				
10/442,858	Removal Composition and Process	Wai Mun Lee	05/20/2003	60937-189-US	8317-189-999
	Cleaning Compositions and Method of				
10/630,300	Use Thereof	Wai Mun Lee	07/30/2003	60937-194-US	8317-194-999
	Compositions and Methods for				
	Rapidly Removing Overfilled				
60/518,337	Substrates	Chelle, et al.	11/10/2003	60937-200-PR	8317-200-888
	CMP Method for Copper, Tungsten,		i		
	Titanium, Polysilicon, and Other				
	Substrates Using Organosulfonic	.	:		
10/690,623	Acids as Oxidizers	Carter, et al.	10/23/2003	60937-202-US	8317-202-999
	PeriodicAcid Compositions for	i			
	Polishing Nobel Metal/High K	Data at L Ossall	00/44/0000	00007.000.00	0047 000 000
60/494,954	Substrates Cerium Oxide Abrasives for Chemical	Robert J. Small	08/14/2003	60937-203-PR	8317-203-888
60/500 000	·	Robert J. Small	10/10/2002	60027 204 DD	0247 204 000
60/509,920	Mechanical Polishing	Robert J. Small	10/10/2003	60937-204-PR	8317-204-888
	Chemical Mechanical Polishing				
	Slurries and Cleaners Containing				
60/516 736	Salicyclic Acid as a Corrosion Inhibitor	Carter, et al.	11/04/2003	60937-206-PR	8317-206-888
00/010,700	Periodic Acid Compositions for	Ourtor, or ai.	1170472000	00301-200-110	0317-200-000
60/494,955	Polishing Ruthenium Substrates	Robert J. Small	08/14/2003	60937-207-PR	8317-207-888
007 10 1,000	Chemical Mechanical Polishing	7,000,701,011,011			0017 207 000
10/683,730	Compositions and Process	Small, et al.	10/10/2003	60937-211-US	8317-211-999
	Alumia Abrasive for Chemical				
60/514,020	Mechanical Polishing	Philippe H. Chelle	10/27/1999	60937-213-PR	8317-213-888
	Chemical Mechanical Polishing			:	
	Slurries and Cleaners Containing				
60/502,951	Salicyclic Acid as a Corrosion Inhibitor	Tamilmani, et al.	09/16/2003	60937-214-PR	8317-214-888
	Compositions for Chemical				
	Mechanical Planarization of Tantalum				
10/665,417	and Tantalum Nitride	Small, et al.	09/22/2003	60937-215-US	8317-215-999
	Alumina Abrasive for Chemical		101001000		0047 040 000
60/526,107	Mechanical Polishing	Chelle, et al.	12/02/2003	60937-216-PR	8317-216-888
60/509,922	Particulate or Particle-Bound	Small of al	10/10/2003	60937-217-PR	8317-217-888
00/009,922	Chelating Agents Particulate or Particle-Bound	Small, et al.	10/10/2003	00931-211-PR	0311-211-000
10/690,626	Chelating Agents	Small, et al.	10/23/2003	60937-217-US	8317-217-999
10/030,020	Chemical Mechanical Polishing of STI		10/20/2000	00337-217-00	0017 217 000
	Features on Semiconductors: Water				
60/533,054	Polishing with Ceria Slurries	Yu, et al.	12/30/2003	60937-223-PR	8317-223-888
	Removal of Post Etch Residues and				
	Copper Contamination From Low-K			•	
	Dielectrics Using Superciritcal CO2				
60/511,949		Jerome Daviot	10/14/2003	60937-225-PR	8317-225-888
	Method and Apparatus for Substrate				1
10/694,999	Pre-Treatment	Lee, et al.	10/29/2003	60937-226-US	8317-226-999

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App_#2;	Title	:::lñventor(s).	Ifilling Date	New Attomey MocketiNo	Former Attorney Docket No.
	Method of Chemically Mechanically				
60/515,450	Polishing Substrates	Brandon S. Scott	10/30/2003	60937-228-PR	8317-228-888